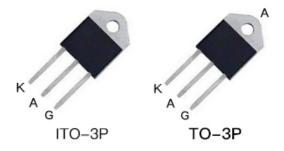


Description

Available in high power packages, the ITO-3P and TO-3P package.

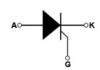
Features

- I_{GT max.} = 50 mA
- Low thermal resistance with clip bonding
- Max. blocking voltage = V_{DRM}, V_{RRM} = 800V



Applications

- General purpose AC switch control
- Control loads in Motor, Fan, and Pump.
- Solenoid drivers
- LED Dimming
- Inrush current limiting circuits



Absolute Maximum Ratings (T_A=25°C)

Rating		Symbol	Value
Peak repetitive off-state voltage (50Hz to 60Hz; Gate open) (Note 1)		V _{DRM} V _{RRM}	800V
On-state RMS current (180° sine wave)		I _{T(RMS)}	55A
Non repetitive surge peak on-state current (full cycle, T initial = 25℃)	F=50Hz, t=10ms	I _{TSM}	300A
I ² t Value for fusing	t _P =10ms	l ² t	1800A ² s
Critical rate of rise of on-state current I _G =2I _{GT}	F=120Hz, T _J =125℃	di/dt	200A/µs
Non repetitive surge peak off-state voltage	t _P =10ms, T _J =25℃	V_{DSM}/V_{RSM}	V _{DRM} /V _{RRM} +100V
Peak gate current	t _P =20µs, T _J =125℃	I _{GM}	8A
Average gate power dissipation	T _J =125℃	$P_{G(AV)}$	1W
Storage junction temperature range		T _{STG}	-40℃ to +150℃
Operating junction temperature range		TJ	-40℃ to +125℃

Note:

V_{DRM} and V_{RRM} for all types can be applied on a continuous basis.
Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



Electrical Characteristics (TJ=25℃, unless otherwise specified)

Parameter	Symbol	Value
$V_D=12V$, $R_L=33\Omega$	I _{GT}	10mA~50mA
V_D = V_{DRM} , R_L =100 Ω , T_J =125 $^{\circ}$ C	V _{GD Min.}	0.2V
I _T =500mA	I _{H Max.} ⁽¹⁾	100mA
I _G =1.2I _{GT}	I _{L Max.}	125mA
V _D =67%V _{DRM} gate open, T _J =125℃	dv/dt _{Min.} (1)	1500V/µs

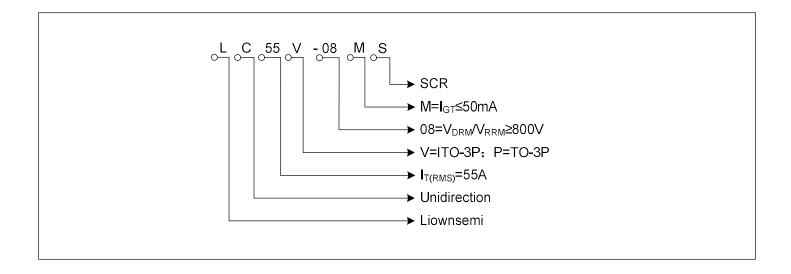
^{1.} for both polarities of A2 referenced to A1

Static Characteristics

Test conditions	Symbol	Value
I _{TM} =55A, t _P =380μs, T _J =25℃	V _{T Max.} ⁽¹⁾	1.6V
Threshold voltage, T _J =125℃	V _{t0 Max.} (1)	0.85V
Dynamic resistance, T _J =125℃	R _{D Max.} ⁽¹⁾	8mΩ
V _{DRM} =V _{RRM} , T _J =25°C	I _{DRM Max.}	5μΑ
V _{DRM} =V _{RRM} , T _J =125℃	I _{RRM Max.}	8mA

^{1.} for both polarities of A2 referenced to A1

Part Number Code

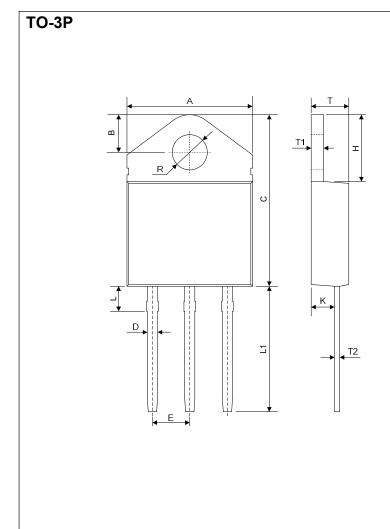




Ordering Information

Part Number	Marking	Package
LC55P-08MS	LC55P-08MS	TO-3P
LC55V-08MS	LC55V-08MS	ITO-3P

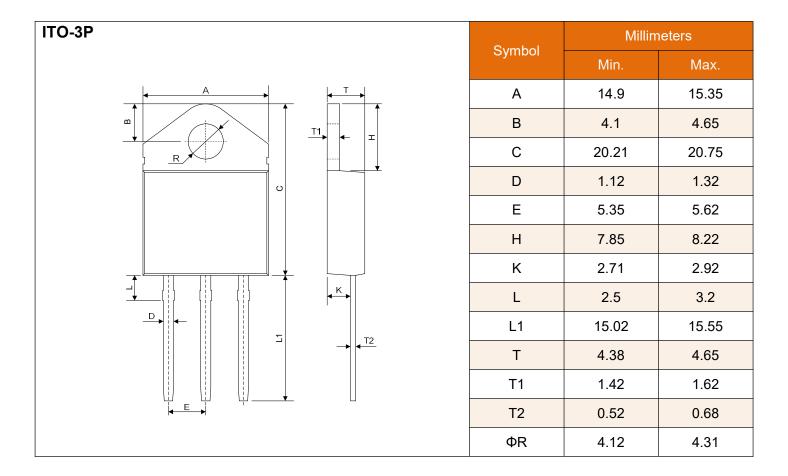
Dimensions



Symbol	Millimeters		
Symbol	Min.	Max.	
А	14.9	15.35	
В	4.1	4.65	
С	20.21	20.75	
D	1.12	1.32	
E	5.35	5.62	
Н	7.85	8.22	
К	2.71	2.92	
L	2.5	3.2	
L1	15.02	15.55	
Т	4.38	4.65	
T1	1.42	1.62	
T2	0.52	0.68	
ΦR	4.12	4.31	



Dimensions



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